

# NVMFD6H852NL-VB Datasheet Dual N-Channel 100V (D-S) MOSFET

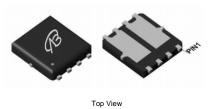
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>		
100	0.018at V <sub>GS</sub> = 10 V	35		
	0.022at V <sub>GS</sub> = 4.5 V	36		

### FEATURES

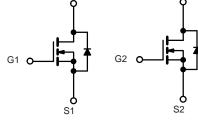
D1

- 175 °C Junction Temperature
- Trench technology Power MOSFET
- Material categorization:





DFN5X6



N-Channel MOSFET N-C

N-Channel MOSFET

D2

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Gate-Source Voltage		V <sub>GS</sub>	±20	V	
Continuous Drain Current (T, = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	1-	35		
Continuous Drain Current $(T_J = T/5 C)$	T <sub>C</sub> = 100 °C	I <sub>D</sub>	20 <sup>a</sup>		
Pulsed Drain Current	I <sub>DM</sub>	105	А		
Continuous Source Current (Diode Conduction)	۱ <sub>S</sub>	76 <sup>a</sup>			
Avalanche Current	I <sub>AS</sub>	82			
Single Avalanche Energy (Duty Cycle $\leq$ 1 %)	L = 0.1 mH	E <sub>AS</sub>	110	mJ	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	136	w	
	T <sub>A</sub> = 25 °C	'D	3 <sup>b</sup> , 8.3 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mauiauna lunation ta Ambianta	$t \le 10 \text{ sec}$	- R <sub>thJA</sub>	15	18	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		60	50	
Maximum Junction-to-Case		R <sub>thJC</sub>	0.85	1.1	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c.  $t \leq 10$  s.

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Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static	·			.,			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	100				
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	1	2	3	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
		V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0 V			1	μA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50		
		V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	1	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	60			А	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.018			
	Б	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.008			
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C		0.010		Ω	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 12A		0.022			
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		60		S	
Dynamic	•						
Input Capacitance	C <sub>iss</sub>			3900			
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V, V_{DS} = 100 V, f = 1 MHz$		470		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			225			
Total Gate Charge <sup>c</sup>	Qg			89	70		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		26		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			23			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			21	25		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 100 V, R <sub>L</sub> = 0.6 $\Omega$		15	25	ne	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$\text{I}_\text{D} \cong$ 50 A, $\text{V}_\text{GEN}$ = 10 V, $\text{R}_g$ = 2.5 $\Omega$		35	50	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (	T <sub>C</sub> = 25 °C)					
Pulsed Current	I <sub>SM</sub>				105	А	
Diode Forward Voltage	$V_{SD}$	$I_{F} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		1	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/µs		4	135	ns	

## **SPECIFICATIONS** ( $T_J = 25 \text{ °C}$ , unless otherwise noted)

Notes:

a. For design aid only; not subject to production testing.

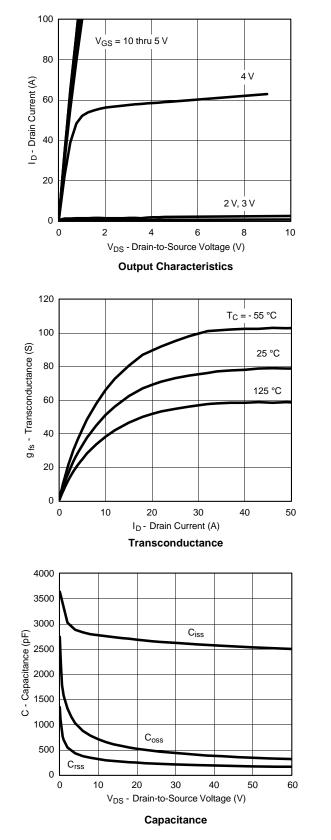
b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

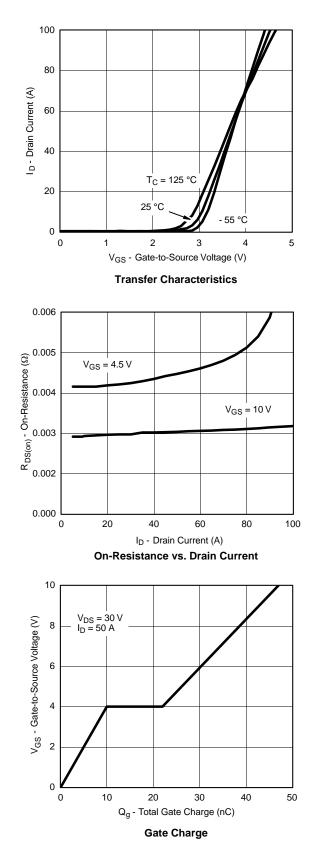
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



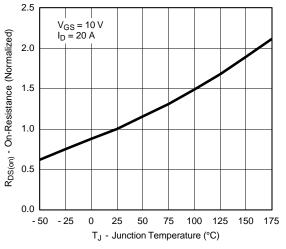
#### TYPICAL CHARACTERISTICS (25 °C unless noted)



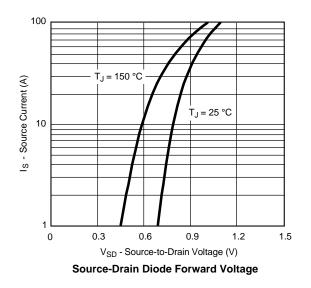




## TYPICAL CHARACTERISTICS (25 °C unless noted)



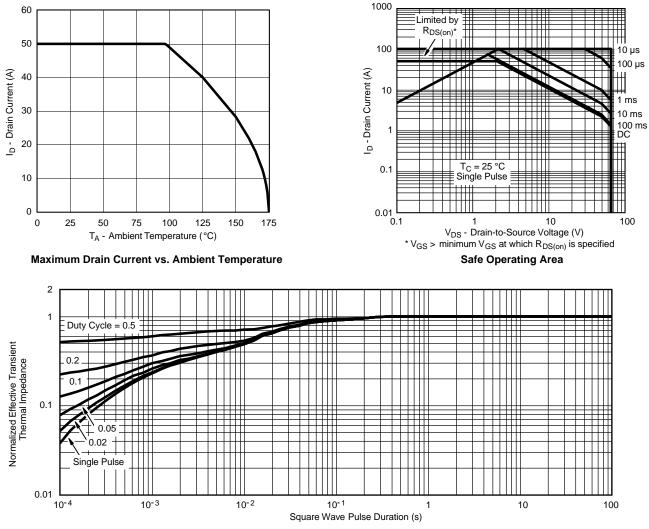
**On-Resistance vs. Junction Temperature** 



# NVMFD6H852NL-VB



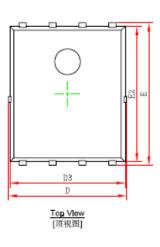
#### **THERMAL RATINGS**

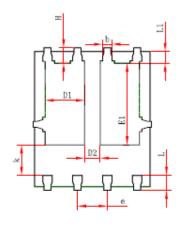


Normalized Thermal Transient Impedance, Junction-to-Case

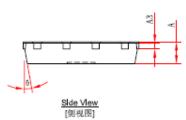


#### PDFNWB5×6-8L-A PACKAGE OUTLINE DIMENSIONS





<u>Bottom Vlew</u> [背视图]



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	0.900	1.000	0.035	0.039	
A3	0.254 REF.		0.010REF.		
D	4.944	5.096	0.195	0.201	
E	5.974	6.126	0.235	0.241	
D1	1.470	1.870	0.058	0.074	
D2	0.470	0.870	0.019	0.034	
E1	3.375	3.575	0.133	0.141	
D3	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
k	1.190	1.390	0.047	0.055	
b	0.350	0.450	0.014	0.018	
e	1.270TYP.		1.270TYP. 0.050TYP.		TYP.
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
θ	10°	12°	10°	12°	



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